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WHAT IS CLAIMED IS:

1. A treatment on a silicon oxynitride, which is applicable to a surface of a silicon oxynitride layer covered by a photo resist layer, the treatment comprising the steps of:

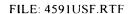
using oxygen plasma to remove a majority of the photo resist layer; and using non-oxygen plasma to overetch in order to remove a residual of the photo resist layer.

- 2. The method to treat a silicon oxynitride surface according to claim 1, wherein the non-oxygen plasma includes inert gas plasma.
- 3. The method to treat a silicon oxynitride surface according to claim 2, wherein the non-oxygen plasma includes argon plasma
- 4. The method to treat a silicon oxynitride surface according to claim 1, wherein a duration of the overetch is approximately 20% to 25% of a duration of the oxygen plasma process.

15 5 5. A method to remove a silicon oxide material, wherein the silicon oxide material is resulted from a reaction between silicon containing materials and oxygen plasma, and the method in removing the silicon oxide material comprising:

an ion bombardment method using inert gas plasma to treat the silicon oxide material.

- 6. The method to remove a silicon oxide material according to claim 5, wherein the inert gas plasma includes argon gas plasma.
- 7. A method to remove a photo resist layer, which is applicable to a photo resist layer covering a silicon oxynitride layer, the method to remove the photo resist layer comprising the steps of:



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using oxygen plasma to remove a majority of the photo resist layer; and using non-oxygen plasma to remove a residual of the photo resist layer.

- 8. The method to remove the photo resist layer according to claim 7, wherein the non-oxygen plasma includes inert gas plasma.
- 9. The method to remove the photo resist layer according to claim 8, wherein the inert gas plasma includes argon plasma.
- 10. The method to remove the photo resist layer according to claim 7, wherein a duration required for a removal of a residual of the photo resist layer is approximately 20 to 25% of a duration required for a removal of a majority of the photo resist layer.